

FORM PTO-1449
(REV. 7.80)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
91-C-127C1SERIAL NO.
09/803,715LIST OF REFERENCES CITED BY APPLICANT
(Use several sheets if necessary)APPLICANT
Jai LiFILING DATE
March 9, 2001GROUP
2823

U. S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (if appropriate)
206	AA 4,829,019	05/09/1989	Mitchell, et al.	437	069	05/12/1987

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
						YES NO
T-2	AB 0123384	31.10.84	EPO	—	—	
f	AC 59-65445	13.4.1984	Japan	—	—	X
	AD 0050634	12.04.1980	Japan	—	—	X
	AE 0271956	09.11.1988	Japan	—	—	X
	AF 0189208	30.07.1986	EPO	—	—	
	AG 0275508	27.07.1988	EPO	—	—	
	AH 0208935	21.01.1987	EPO	—	—	
	AI WO 83/02197	23.06.1987	PCT	—	—	
T-3	AJ 0401174	05.12.1990	EPO	—	—	

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

T-1	AK	"Silicon Processing for the VLSI Era," Vol. 2, : Process Integration by Stanley Wolf, Ph.D., 1990, pp. 38-41.
T-2	AL	International Electron Devices Meeting, Dec. 1982, Washington, D.C., "Electrical Properties of MOS Devices Made with Silo Technology," J. Hui, T.Y. Chiu, S. Wong and W.G. Oldham, IEEE, pp. 220-223.
T-3	AM	International Electron Devices Meeting, Dec. 8, 1980, Washington, D.C., "Selective Polysilicon Oxidation Technology for Defect Free Isolation," Junichi Matsanaga, Naohiro Matsukawa, Hiroshi Nozawa, and Susumu Kohyama, IEEE, pp. 565-568.
T-4	AN	"Under Field Oxidation Dopant Enhancement (UFDE) for CMOS and BiCMOS Technology," Extended Abstracts of the 22nd (1990) International Conference on Solid State Devices and Mater 1990, pp. 649-652.

EXAMINER

T. DANG

DATE CONSIDERED

5/29/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line if not in conformance and not considered. Include copy of this form with next communication to applicant.